



P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)			
	0.00875 at V _{GS} = - 4.5 V	- 14			
- 20	0.01075 at V _{GS} = - 2.5 V	- 12			
	0.0135 at V _{GS} = - 1.8 V	- 11			

FEATURES

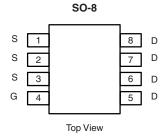
- Halogen-free Option Available
- TrenchFET® Power MOSFET

Pb-free

RoHS

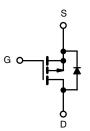
APPLICATIONS

- · Game Station
 - Load Switch



Ordering Information: Si4421DY-T1-E3 (Lead (Pb)-free)

Si4421DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter	Symbol	10 s	Steady State	Unit		
Drain-Source Voltage		V_{DS}	- 20		V	
Gate-Source Voltage		V _{GS}	± 8			
Continuous Drain Current (T _{.I} = 150 °C) ^a	T _A = 25 °C	- I _D	- 14	- 10	A	
Continuous Diam Current (1) = 150 °C)	T _A = 70 °C		- 11.5	- 8		
Pulsed Drain Current		I _{DM}	- 40		A	
Continuous Source Current (Diode Conduction) ^a		I _S	- 2.7	- 1.36		
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	3.0	1.5	W	
waxiinani i owei Dissipation	T _A = 70 °C		1.9	0.95		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maniana lunation to Ambienti	t ≤ 10 s	- R _{thJA}	33	42	°C/W
Maximum Junction-to-Ambient ^a	Steady State		70	85	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	16	21	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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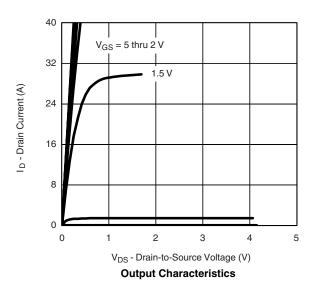
SPECIFICATIONS $T_J = 25$	°C, unless	otherwise noted					
Parameter Sym		Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -850 \mu A$	- 0.4		- 0.8	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current		V_{DS} = - 20 V, V_{GS} = 0 V, T_J = 70 °C			- 10	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 30			Α	
		V _{GS} = - 4.5 V, I _D = - 14 A		0.007	0.00875		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 12 A		0.0085	0.01075	Ω	
		V _{GS} = - 1.8 V, I _D = - 11 A		0.011	0.0135		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 14 A		55		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 2.7 A, V _{GS} = 0 V		- 0.6	- 1.1	V	
Dynamic ^b							
Total Gate Charge	Q_g			82	125		
Gate-Source Charge	Q _{gs} V _D	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -14 \text{ A}$		10		nC	
Gate-Drain Charge	Q_{gd}			27			
Gate Resistance	R_{g}			3		Ω	
Turn-On Delay Time	t _{d(on)}			45	70		
Rise Time t _r		V_{DD} = - 10 V, R_L = 10 Ω		90	140		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 1 A, V_{GEN} = - 4.5 V, R_G = 6 Ω		350	550	ns	
Fall Time	t _f			170	260	113	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.1 A, dl/dt = 100 A/μs		135	210		

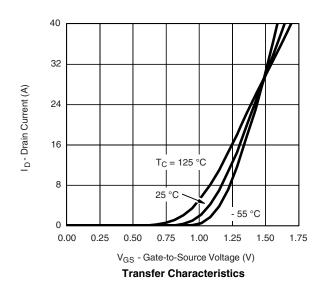
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

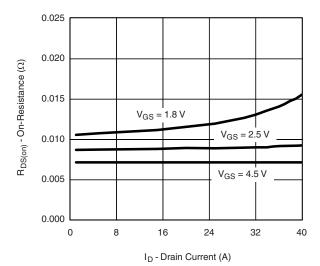




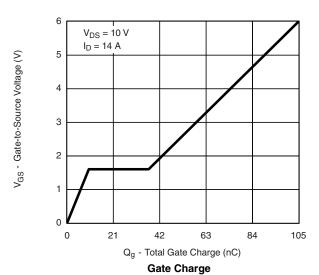


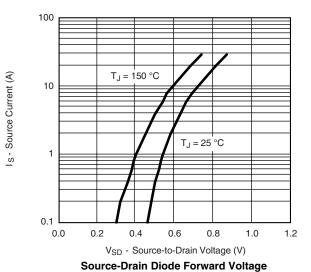


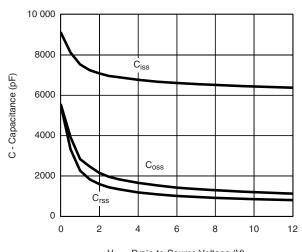
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Drain Current

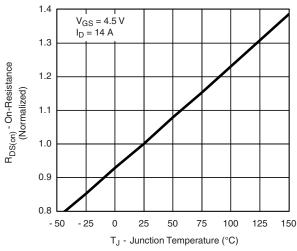




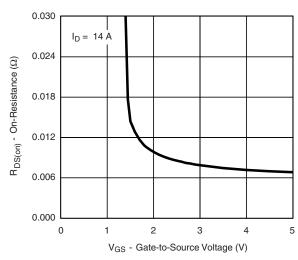


V_{DS} - Drain-to-Source Voltage (V)





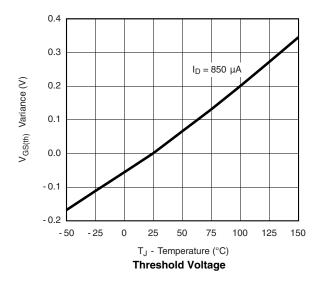
On-Resistance vs. Junction Temperature

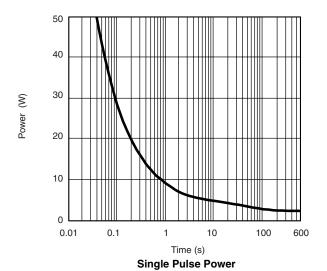


On-Resistance vs. Gate-to-Source Voltage

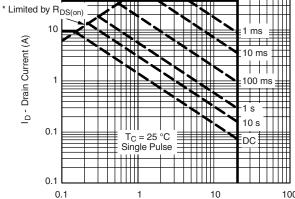
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



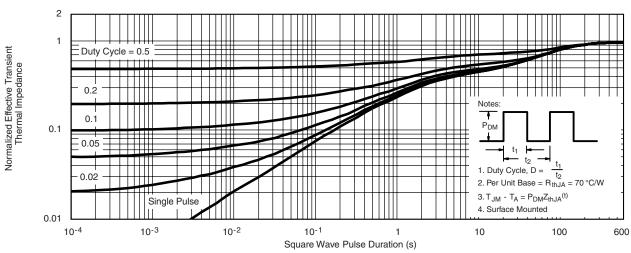


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V_{DS} - Drain-to-Source Voltage (V)

Safe Operating Area, Junction-to-Case

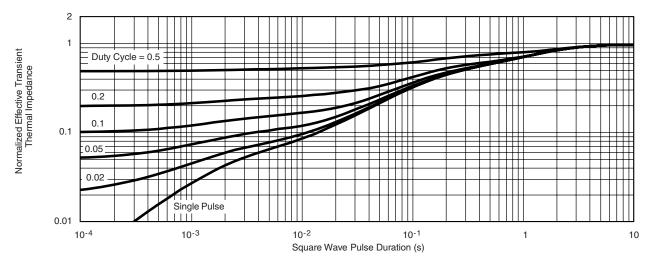


Normalized Thermal Transient Impedance, Junction-to-Ambient

^{*} V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

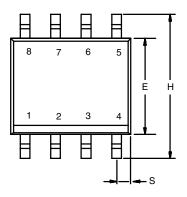


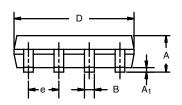
Normalized Thermal Transient Impedance, Junction-to-Foot

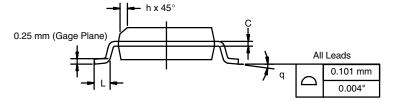
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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIMETERS		MILLIMETERS INCHES		
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
Е	3.80	4.00	0.150	0.157	
е	1.27 BSC		0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I. 11-Sep-06					

DWG: 5498

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APPLICATION NOTE



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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